

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently amended) A semiconductor device production method comprising ~~the steps~~ of:

- (a) forming an insulative film on an underlying substrate;
- (b) forming a semiconductor layer on the insulative film;
- (c) bonding a flexible substrate onto the semiconductor layer; and
- (d) separating the semiconductor layer on the flexible substrate from the insulative

film on the underlying substrate; and

wherein the semiconductor layer has a thickness of 25 μ m to 100 μ m.

2. (Original) A semiconductor device production method as set forth in claim 1,

wherein the semiconductor layer formed in the step (b) is a crystalline Si layer,

wherein the step (b) comprises the steps of:

- (b1) forming an a-Si layer on the insulative film;
- (b2) forming a catalytic layer on the a-Si layer;
- (b3) crystallizing the a-Si layer in contact with the catalytic layer into the crystalline Si

layer through a catalytic reaction; and

- (b4) removing the catalytic layer.

3. (Original) A semiconductor device production method as set forth in claim 1, further comprising the step of forming a semiconductor element in the semiconductor layer after the step

(b).

4. (Currently amended) A semiconductor device production method comprising:

(a) forming an insulative film on an underlying substrate;

(b) forming a semiconductor layer on the insulative film;

(c) bonding a flexible substrate onto the semiconductor layer; and

(d) separating the semiconductor layer on the flexible substrate from the insulative film on the underlying substrate.

wherein the semiconductor layer formed in the step (b) is a crystalline Si layer,

wherein the step (b) comprises the steps of:

(b1) forming an a-Si layer on the insulative film;

(b2) forming a catalytic layer on the a-Si layer;

(b3) crystallizing the a-Si layer in contact with the catalytic layer into the crystalline Si layer through a catalytic reaction; and

(b4) removing the catalytic layer

~~A semiconductor device production method as set forth in claim 2,~~ wherein the step (b1) comprises the step of patterning the a-Si film to segment the a-Si film after the formation of the a-Si film.

5. (Currently amended) A semiconductor device production method comprising:

(a) forming an insulative film on an underlying substrate;

(b) forming a semiconductor layer on the insulative film;

(c) bonding a flexible substrate onto the semiconductor layer; and

(d) separating the semiconductor layer on the flexible substrate from the insulative film on the underlying substrate.

wherein the semiconductor layer formed in the step (b) is a crystalline Si layer,

wherein the step (b) comprises the steps of:

(b1) forming an a-Si layer on the insulative film;

(b2) forming a catalytic layer on the a-Si layer;

(b3) crystallizing the a-Si layer in contact with the catalytic layer into the crystalline Si layer through a catalytic reaction; and

(b4) removing the catalytic layer

~~A semiconductor device production method as set forth in claim 2~~, wherein the step (b2) comprises the step of patterning the catalytic layer after the formation of the catalytic layer.

6. (Original) A semiconductor device production method as set forth in claim 1, wherein the insulative film is cleaved or etched away for the separation in the step (d).

7. (Currently amended) A semiconductor device produced by a semiconductor device production method as recited in claim ~~[[1]]~~ 4, wherein the semiconductor layer has a thickness of 25 μ m to 100 μ m.

8. (Currently amended) A semiconductor device as set forth in claim ~~[[7]]~~ 1, wherein the semiconductor layer is a crystalline Si layer.

9. (Currently amended) A semiconductor device production method comprising ~~the steps~~
~~of~~:

(e) forming an insulative film on an underlying substrate and patterning ~~patterning~~ the insulative film to form a recess in the insulative film;

(f) forming a semiconductor layer on the insulative film, the semiconductor layer having a thick film portion located on a portion of the insulative film formed with the recess and a thin film portion located on a portion of the insulative film adjacent to the recess;

(g) separating the underlying substrate from the semiconductor layer ~~on the flexible substrate from the insulative film on the underlying substrate~~; and

(h) bonding a flexible substrate to the ~~onto a surface of the separated~~ semiconductor layer in place of the separated ~~which has been opposed to the~~ underlying substrate.

10. (Original) A semiconductor device production method as set forth in claim 9,

wherein the semiconductor layer formed in the step (f) is a crystalline Si layer,

wherein the step (f) comprises the steps of:

(f1) forming an a-Si layer on the insulative film;

(f2) forming a catalytic layer on the a-Si layer;

(f3) patterning the catalytic layer so as to leave a portion of the catalytic layer on the a-Si layer in the recess;

(f4) crystallizing the a-Si layer in contact with the catalytic layer into the crystalline Si layer through a catalytic reaction; and

(f5) removing the catalytic layer.

11. (Original) A semiconductor device production method as set forth in claim 9, further comprising the step of forming a semiconductor element in at least one of the thick film portion and the thin film portion after the step (f).

12. (Original) A semiconductor device production method as set forth in claim 9, further comprising the step of forming a circuit having a high breakdown voltage element in the thick film portion and forming a circuit having no high breakdown voltage element in the thin film portion after the step (f).

13. (Original) A semiconductor device production method as set forth in claim 9, wherein the insulative film is cleaved or etched away for the separation in the step (g).

14. (Original) A semiconductor device produced by a semiconductor device production method as recited in claim 9, wherein the semiconductor layer has a thickness of 25 μ m to 50 μ m.

15. (Original) A semiconductor device as set forth in claim 14, wherein the semiconductor layer is a crystalline Si layer.